

L Number	Hits	Search Text	DB	Time stamp
20	1	10/628550	USPAT; US-PGPUB	2004/07/13 14:00
21	1	09/521512	USPAT; US-PGPUB	2004/07/13 14:05
22	1		USPAT	2004/07/13 14:00
23	1		USPAT	2004/07/13 14:01
24	1		USPAT	2004/07/13 14:04
25	1		USPAT	2004/07/13 14:05
26	530	(semiconductor adj laser) with ("InP" near5 substrate)	USPAT; US-PGPUB	2004/07/13 14:41
27	36	(semiconductor adj laser) with (("InP" near5 substrate) with (groove via hole trench recess))	USPAT; US-PGPUB	2004/07/13 14:10
28	55	(semiconductor adj laser) with (("InP" near5 layer) with (groove via hole trench recess))	USPAT; US-PGPUB	2004/07/13 14:13
29	5	((semiconductor adj laser) with (("InP" near5 layer) with (groove via hole trench recess))) and ((active adj region) near5 (groove via hole trench recess))	USPAT; US-PGPUB	2004/07/13 14:13
30	502	(semiconductor adj laser) with ("InP" near5 layer)	USPAT; US-PGPUB	2004/07/13 14:15
31	162	((semiconductor adj laser) with ("InP" near5 layer)) and ((groove recess hole via trench) with ("InP" near5 layer))	USPAT; US-PGPUB	2004/07/13 14:17
32	3246	"32" and ((groove recess hole via trench) with (active adj region))	USPAT; US-PGPUB	2004/07/13 14:18
33	29	(((semiconductor adj laser) with ("InP" near5 layer)) and ((groove recess hole via trench) with ("InP" near5 layer))) and ((groove recess hole via trench) with (active adj region))	USPAT; US-PGPUB	2004/07/13 14:23
34	7	layer with ("InAsP" with (active adj region))	USPAT; US-PGPUB	2004/07/13 14:25
35	4	("InAsP" with (active adj region)).clm	USPAT; US-PGPUB	2004/07/13 14:27
36	2	("InAsP" with (active adj region)) with groove	USPAT; US-PGPUB	2004/07/13 14:28
37	0	("InAsP" with (active adj region)) with recess	USPAT; US-PGPUB	2004/07/13 14:28
38	0	("InAsP" with (active adj region)) with trench	USPAT; US-PGPUB	2004/07/13 14:28
39	1	("InAsP" with (active adj region)) with hole	USPAT; US-PGPUB	2004/07/13 14:30
40	0	"InP" with (arsenic with phosphorous)	USPAT; US-PGPUB	2004/07/13 14:31
41	21	"InP" with (arsenic with phosphorous)	USPAT; US-PGPUB	2004/07/13 14:32
42	6	("InP" with (arsenic with phosphorous)) with layer	USPAT; US-PGPUB	2004/07/13 14:33
43	19	("InP" with (arsenic with phosphorus)) with layer	USPAT; US-PGPUB	2004/07/13 14:41
44	23	("InP" with thermal\$4) with active adj region	USPAT; US-PGPUB	2004/07/13 14:38
45	674	(semiconductor adj laser) with ("InP" near5 (layer substrate))	USPAT; US-PGPUB	2004/07/13 14:42
46	712	(trench via hole recess groove) with ("InP" near5 (layer substrate))	USPAT; US-PGPUB	2004/07/13 14:44
47	408	(semiconductor adj laser) and ((trench via hole recess groove) with ("InP" near5 (layer substrate)))	USPAT; US-PGPUB	2004/07/13 14:46
48	23	((semiconductor adj laser) and ((trench via hole recess groove) with ("InP" near5 (layer substrate)))) and (active adj region) with ((trench via hole recess groove) with ("InP" near5 (layer substrate)))	USPAT; US-PGPUB	2004/07/13 14:46